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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/750,073	12/31/2003	Shen-Kan Hsiung	003-03-033	1871
35870 7	7590 02/24/2005		EXAMINER	
APEX JURIS	S, PLLC VATER LANE NORTH	RAO, SHRINIVAS H		
SEATTLE, W		IEASI	ART UNIT	PAPER NUMBER
			2814	
			DATE MAILED: 02/24/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)	,		
Office Action Summary		10/750,073	HSIUNG ET AL.			
		Examiner	Art Unit			
		Steven H. Rao	2814			
Period fo	The MAILING DATE of this communication Reply	on appears on the cover sheet w	ith the correspondence address	s		
THE - Exte after - If the - If NO - Failt Any	ORTENED STATUTORY PERIOD FOR MAILING DATE OF THIS COMMUNICAT insions of time may be available under the provisions of 37 SIX (6) MONTHS from the mailing date of this communicae a period for reply specified above is less than thirty (30) day to period for reply is specified above, the maximum statutory are to reply within the set or extended period for reply will, by reply received by the Office later than three months after the patent term adjustment. See 37 CFR 1.704(b).	CFR 1.136(a). In no event, however, may a tition.  In a reply within the statutory minimum of thir period will apply and will expire SIX (6) MON by statute, cause the application to become Al	reply be timely filed  ty (30) days will be considered timely.  NTHS from the mailing date of this communi  BANDONED (35 U.S.C. § 133).	iication.		
Status						
1) 又	Responsive to communication(s) filed or	n 31 December 2003.				
· · · · · · · · · · · · · · · · · · ·	This action is <b>FINAL</b> . 2b)⊠ This action is non-final.					
3) 🗌	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposit	ion of Claims					
5)	Claim(s) 1-8 is/are pending in the application of the above claim(s) is/are with claim(s) is/are allowed.  Claim(s) 1-8 is/are rejected.  Claim(s) is/are objected to.  Claim(s) are subject to restriction	ithdrawn from consideration.				
Applicat	ion Papers					
10)⊠	The specification is objected to by the Ex The drawing(s) filed on <u>31 December 200</u> Applicant may not request that any objection Replacement drawing sheet(s) including the The oath or declaration is objected to by	03 is/are: a)  accepted or b)  to the drawing(s) be held in abeyal correction is required if the drawing	nce. See 37 CFR 1.85(a). (s) is objected to. See 37 CFR 1.1	121(d).		
Priority (	under 35 U.S.C. § 119					
a)	Acknowledgment is made of a claim for for All b) Some * c) None of:  1. Certified copies of the priority doct 2. Certified copies of the priority doct 3. Copies of the certified copies of the application from the International I	uments have been received. uments have been received in A ne priority documents have been Bureau (PCT Rule 17.2(a)).	Application No  received in this National Stage	e		
Attachmer	nt(s)					
	ce of References Cited (PTO-892)		Summary (PTO-413) s)/Mail Date			
3) Infor	ce of Draftsperson's Patent Drawing Review (PTO-9 mation Disclosure Statement(s) (PTO-1449 or PTO er No(s)/Mail Date		nformal Patent Application (PTO-152)	ı		

#### **DETAILED ACTION**

## **Priority**

The Application as currently filed does not claim priority from any previously filed Application. Therefore, currently the earliest available filling date is the U.S. filling date namely December 31, 2003.

### Information Disclosure Statement

Acknowledgment is made of receipt of Applicant's Information Disclosure Statement (PTO-1449) filled on 12/31/2003.

The references submitted on 12/31/2003 are acknowledged. All the cited references have been considered.

Presently the single sheet of 1449 submitted does not list any references thereon. Therefore an initialed 1449 can be enclosed herewith.

It is suggested that Applicants' include a 1449 listing the references submitted with the IDS of 12/31/2003 thereon, which will be initialed and mailed with the next Office Action.

However the foreign patents and documents (in languages other than English and without a translation) cited by applicant are considered to the extent that could be understood from the abstract and drawings.

## Claim Objections

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Claims 1-8 are objected to under 35 U.S.C. 112, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

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In claim 1 the phrase "fabricating said readout circuit device of said array pH sensor according to the typical process for making semiconductors" renders the claim indefinite because the term "typical process" is characterized according to applicant's own definition (e.g. specification page 9 lines 14-15) merely means "conventional" or "well known" process; if applicant desires to patent detailed controls over the process they should be affirmatively recited in the claim; if all that asserted as invention is hybrid pH sensor as such,. It is suggested that applicants use either of the terms 'conventional "or "well known "instead of "typical. "

Claims 2-8 are objected to for directly/indirectly depending upon objected to claim 1.

Appropriate correction is required.

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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Claims 1-8 rejected under 35 U.S.C. 103(a) as being unpatentable over Hsiung et al. (U.S Patent No. 6,236,075, herein after Hsiung) in view of Kinlen et al. (U.S. Patent No. 5,110,441, herein after Kinlen).

With respect to claim 1 Hsiung describes a method for fabricating an array pH sensor and a readout circuit device of said array PH sensor, comprising: depositing a non-conductive PH sensing film onto an non-insulated substrate, (Hsiung figure2G#25, col. 3 lines 38-40 and claim 8) thereby fabricating a separate array PH sensor and detecting the PH value of the solution by using said array PH sensor; (Hsiung figure 4, col. 3 lines 54 to 62).

Hsiung does not specifically describe fabricating a readout circuit device of said array PH sensor according to the typical processes for making semiconductors.

However, Kinlen, a patent from the same field of endeavor describes in figures 26, 27 etc. describe fabricating a readout circuit device of said array PH sensor according to the typical processes for making semiconductors to provide acceptable drift of electrode potential and dramatically improve performance of the system and provide an electrode with constant Nernstian response.

Therefore it would have been obvious to one of ordinary skill in the art at the time of the invention to include Kinlen's readout circuit device in Husing's method, the motivation to make the above combination is to provide acceptable drift of electrode potential and dramatically improve performance of the system and provide an electrode with constant Nernstian response. (Kinlen col. 21 lines 43 to 51).

The remaining limitations of claim 1:

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and combining said array pH sensor and said readout circuit device as a hybrid array pH sensor. (Kinlen figure 26, col. 30 line 59 to col. 31 col. 32 line 14).

With respect to claim 2 Hsiung describes for fabricating an array PH sensor and a readout circuit device of said array pH sensor according to claim 1, wherein said array PH sensor is fabricated by the following steps: Step I: providing a substrate; (Hsuing figure 2a # 20) Step 2: growing an A1 film by using a metallic mask and a vacuum evaporation machine; (Hsuing figure 2 E col. 3 lines 23 to 25, Hsiung col. 14 line 66) Step 3: growing a SnO2 film by using a metallic mask and a sputter machine; (Hsuing figure 2G, col. 3 lines line 31, 38-40) and Step 4: encapsulating the resulting product with epoxy resin. (Husing Figure 2 H, col. 3 lines 41 to 46).

With respect to claim 3 Hsuing describes the method for fabricating an array PH sensor and a readout circuit device of said array pH sensor according to claim 1, wherein said array pH sensor has a tin dioxide/metal silicon dioxide multi-layer structure or a tin dioxide/indium tin oxide/glass multi-layer structure. (Hsuing figure 2 H, layers 21,25, etc., Abstract last two lines from bottom, col. 2 lines 5-7)

With respect to claim 4 Hsiung describes the method for fabricating an array PH sensor and a readout circuit device of said array PH sensor according to claim 1, wherein said array PH sensor comprises a pre-readout circuit, (Kinlen figure 26 the circuit formed by 402,to 408) a multiplexer, a rear end buffer circuit (Kinlein fig. 26, #408, digital controller buffers the input current and then converts the current) and an amplifier circuit. (Kinlen fig. 26 #404).

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With respect to claim 5 Hsiung describes the method for fabricating an array pH sensor and a readout circuit device of said array pH sensor according to claim 2, wherein said substrate is selected from a glass substrate, a silicon substrate, a ceramic substrate or a polymeric substrate. (Hsuing line 64-silsicon, Kinlen col. 20 ex. 1 – ceramic ,glass ,etc.)

With respect to claims 6 and 7 Hsiung describes the method for fabricating an array pH sensor and a readout circuit device of said array PH sensor according to claim 3, wherein said tin dioxide/metal/silicon dioxide structure is formed by depositing an aluminum layer and a tin dioxide layer onto said substrate, and encapsulating the resulting structure with epoxy resin to form a opening channel, (see above rejections) wherein a conducting line is led out via said aluminum layer. (Hsuing figure 2E, etc. # 24 a-aluminum plugs, col 3 line 26).

With respect to claim 8 Hsiung describes the method for fabricating an array pH sensor and a readout circuit device of said array PH sensor according to claim 4, wherein said readout circuit device of said array PH sensor receives different signals ( Hsiung figure 26 404-408 all receive different signals) and amplifies these signals for determination ( Hsiung fig. 26 404 ) such that when the multiplexer is modified, ( Hsuing fig. 26 # 406 , col. 31 lines 10-25) a variety of array sensors can be fabricated ( Kinlen col. 1 line 17, etc.) and said array sensor can be applied for fabrication of potentiometeric sensor.

The recitation "said array sensor can be applied for fabrication of photiometeric sensor is taken to be an intended use recitation and does not differentiate the apparatus

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obtained by recited method from the apparatus obtained by the prior art method satisfying the claimed structural limitations. Ex parte Masham 2 USPQ 2d 1647 ( !987) .

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven H. Rao whose telephone number is (571) 272-1718 can normally be reached on 8.00 to 5.00.

The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Steven H. Rao

Patent Examiner

Feb. 19, 2005.